

DATA SHEET

For a complete data sheet, please also download:

- The IC04 LOCMOS HE4000B Logic Family Specifications HEF, HEC
- The IC04 LOCMOS HE4000B Logic Package Outlines/Information HEF, HEC

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

HEF4066B gates Quadruple bilateral switches

Product specification
File under Integrated Circuits, IC04

January 1995

Quadruple bilateral switches

HEF4066B gates

DESCRIPTION

The HEF4066B has four independent bilateral analogue switches (transmission gates). Each switch has two input/output terminals (Y/Z) and an active HIGH enable input (E). When E is connected to V_{DD} a low impedance bidirectional path between Y and Z is established (ON condition). When E is connected to V_{SS} the switch is

disabled and a high impedance between Y and Z is established (OFF condition).

The HEF4066B is pin compatible with the HEF4016B but exhibits a much lower ON resistance. In addition the ON resistance is relatively constant over the full input signal range.

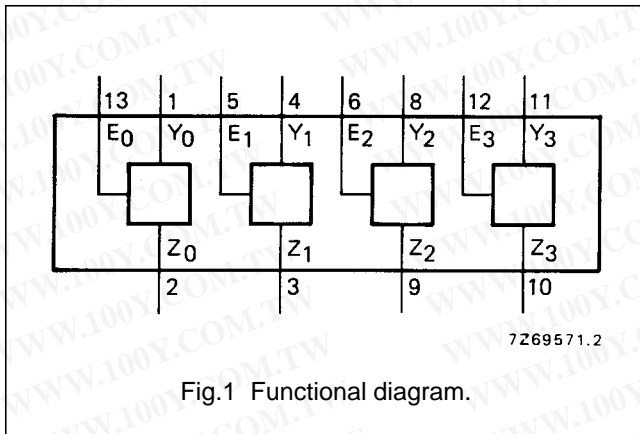


Fig.1 Functional diagram.

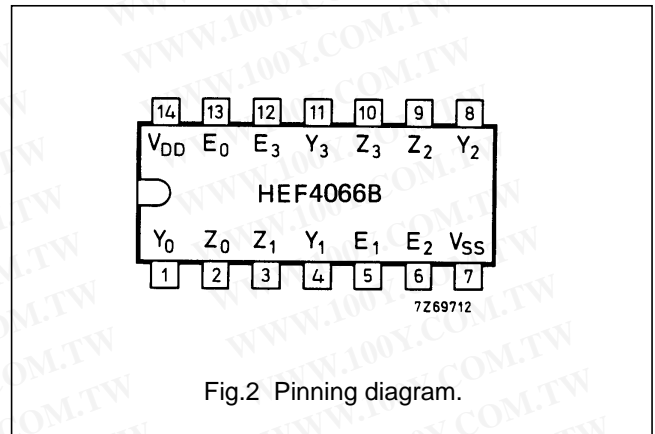


Fig.2 Pinning diagram.

- HEF4066BP(N): 14-lead DIL; plastic (SOT27-1)
- HEF4066BD(F): 14-lead DIL; ceramic (cerdip) (SOT73))
- HEF4066BT(D): 14-lead SO; plastic (SOT108-1)
- (): Package Designator North America

PINNING

- E_0 to E_3 enable inputs
- Y_0 to Y_3 input/output terminals
- Z_0 to Z_3 input/output terminals

APPLICATION INFORMATION

An example of application for the HEF4066B is:

- Analogue and digital switching

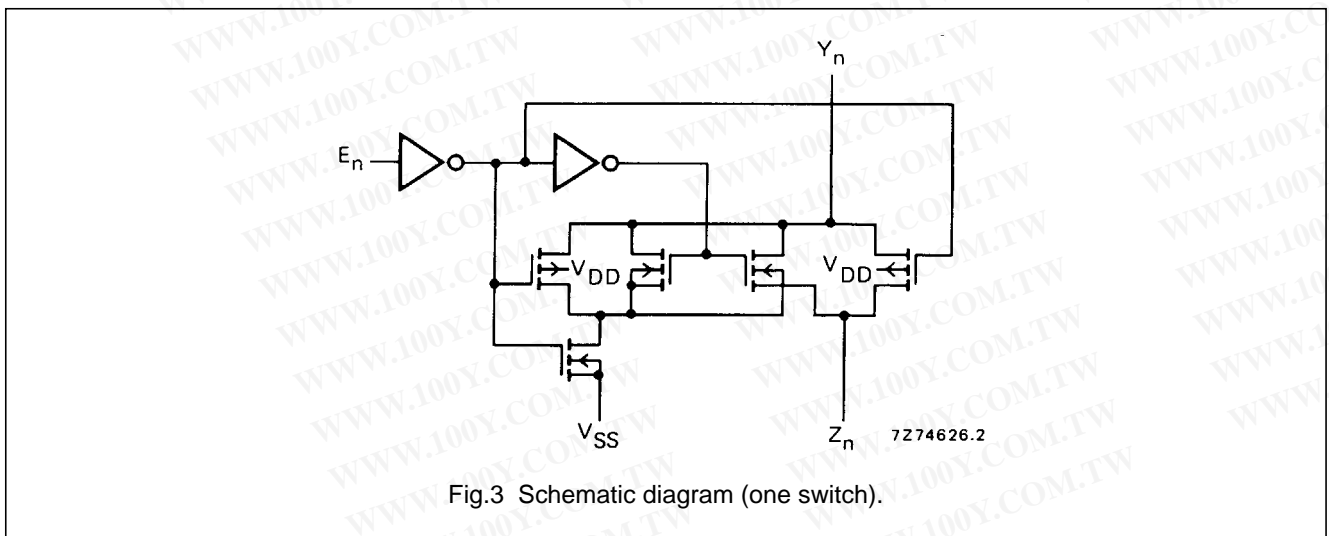


Fig.3 Schematic diagram (one switch).

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RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Power dissipation per switch

P max. 100 mW

For other RATINGS see Family Specifications

DC CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$

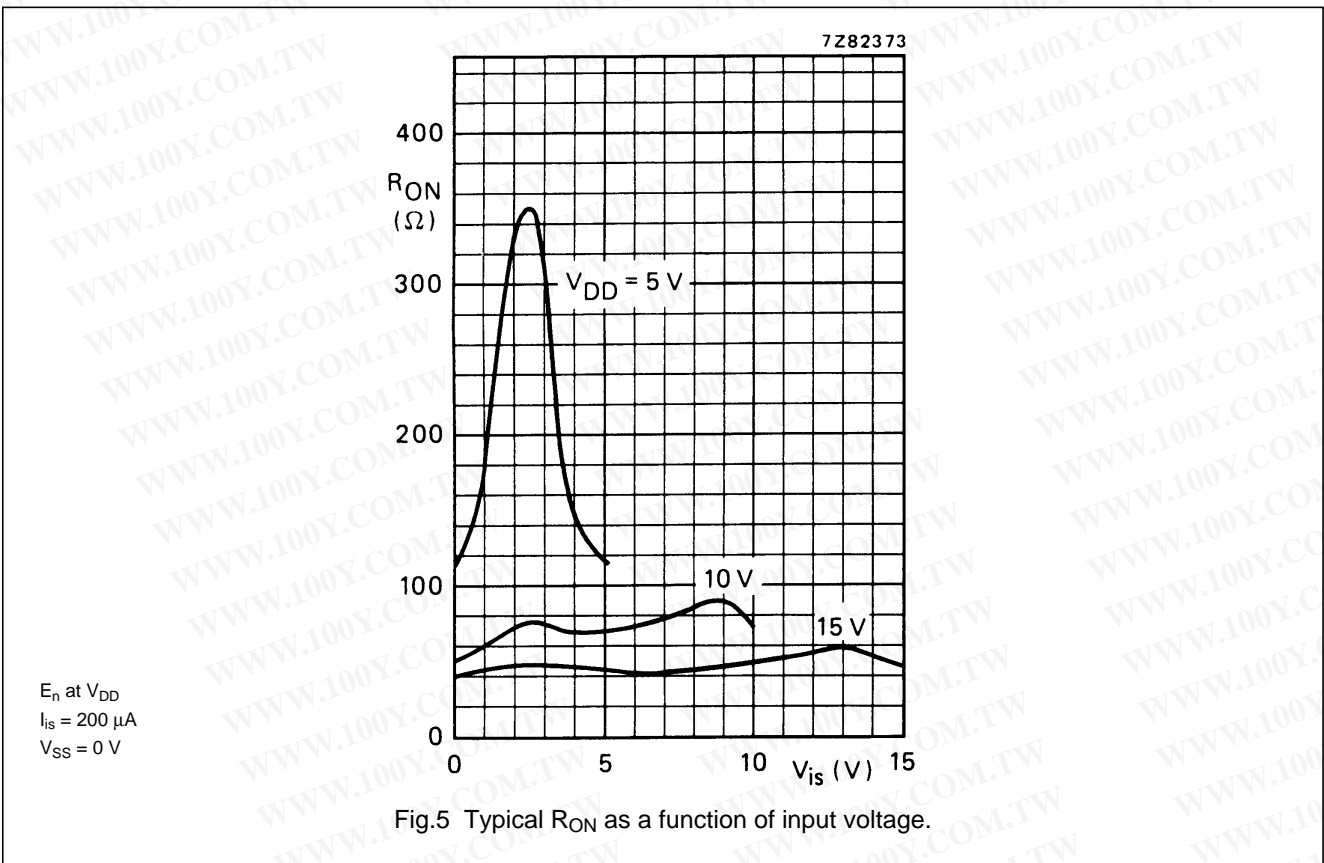
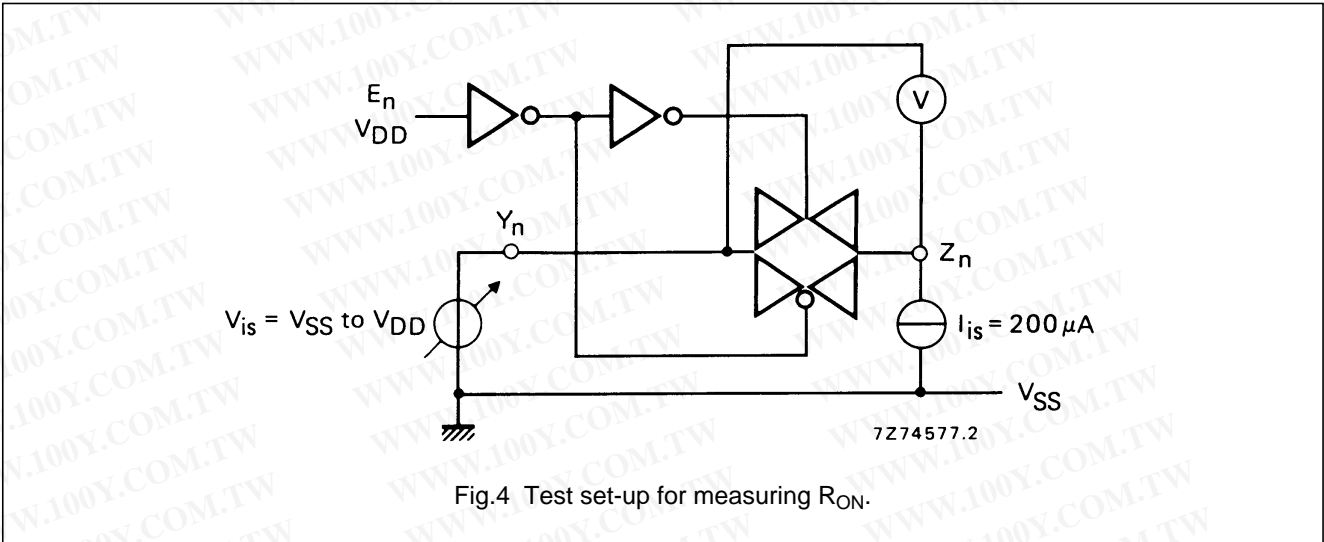
	V_{DD} V	SYMBOL	$T_{amb} (^{\circ}\text{C})$			CONDITIONS
			MIN.	TYP.	MAX.	
ON resistance	5	R_{ON}	–	350	2500	E_n at V_{DD} $V_{is} = V_{SS}$ to V_{DD} see Fig.4
	10		–	80	245	
	15		–	60	175	
ON resistance	5	R_{ON}	–	115	340	E_n at V_{DD} $V_{is} = V_{SS}$ see Fig.4
	10		–	50	160	
	15		–	40	115	
ON resistance	5	R_{ON}	–	120	365	E_n at V_{DD} $V_{is} = V_{DD}$ see Fig.4
	10		–	65	200	
	15		–	50	155	
' Δ ' ON resistance between any two channels	5	ΔR_{ON}	–	25	–	E_n at V_{DD} $V_{is} = V_{SS}$ to V_{DD} see Fig.4
	10		–	10	–	
	15		–	5	–	
OFF state leakage current, any channel OFF	5	I_{OZ}	–	–	–	E_n at V_{SS}
	10		–	–	–	
	15		–	–	200	
E_n input voltage LOW	5	V_{IL}	–	2,25	1	$I_{is} = 10\text{ }\mu\text{A}$ see Fig.9
	10		–	4,50	2	
	15		–	6,75	2	

	V_{DD} V	SYMBOL	$T_{amb} (^{\circ}\text{C})$			CONDITIONS
			–40 MAX.	+25 MAX.	+85 MAX.	
Quiescent device current	5	I_{DD}	1,0	1,0	7,5	$V_{SS} = 0$; all valid input combinations; $V_I = V_{SS}$ or V_{DD}
	10		2,0	2,0	15,0	
	15		4,0	4,0	30,0	
Input leakage current at E_n	15	$\pm I_{IN}$	–	300	1000	E_n at V_{SS} or V_{DD}

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NOTE

To avoid drawing V_{DD} current out of terminal Z, when switch current flows into terminals Y, the voltage drop across the bidirectional switch must not exceed 0,4 V. If the switch current flows into terminal Z, no V_{DD} current will flow out of terminals Y, in this case there is no limit for the voltage drop across the switch, but the voltages at Y and Z may not exceed V_{DD} or V_{SS} .

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AC CHARACTERISTICS ^{(1), (2)}

$V_{SS} = 0\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; input transition times $\leq 20\text{ ns}$

	V_{DD} V	SYMBOL	TYP.	MAX.		
Propagation delays $V_{is} \rightarrow V_{os}$ HIGH to LOW	5	t_{PHL}	10	20	ns	
	10		5	10	ns	
	15		5	10	ns	
	5		t_{PLH}	10	20	ns
	10			5	10	ns
	15			5	10	ns
Output disable times $E_n \rightarrow V_{os}$ HIGH	5	t_{PHZ}	80	160	ns	
	10		65	130	ns	
	15		60	120	ns	
	5		t_{PLZ}	80	160	ns
	10			70	140	ns
	15			70	140	ns
Output enable times $E_n \rightarrow V_{os}$ HIGH	5	t_{PZH}	40	80	ns	
	10		20	40	ns	
	15		15	30	ns	
	5		t_{PZL}	45	90	ns
	10			20	40	ns
	15			15	30	ns
Distortion, sine-wave response	5		0,25		%	
	10		0,04		%	
	15		0,04		%	
Crosstalk between any two channels	5		–		MHz	
	10		1		MHz	
	15		–		MHz	
Crosstalk; enable input to output	5		–		mV	
	10		50		mV	
	15		–		mV	
OFF-state feed-through	5		–		MHz	
	10		1		MHz	
	15		–		MHz	
ON-state frequency response	5		–		MHz	
	10		90		MHz	
	15		–		MHz	

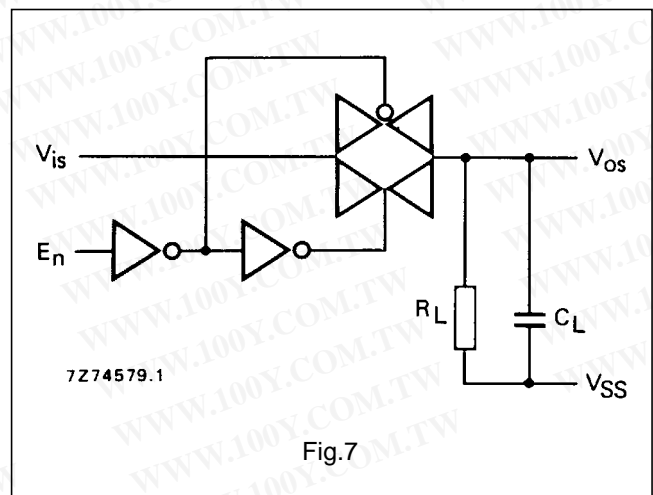
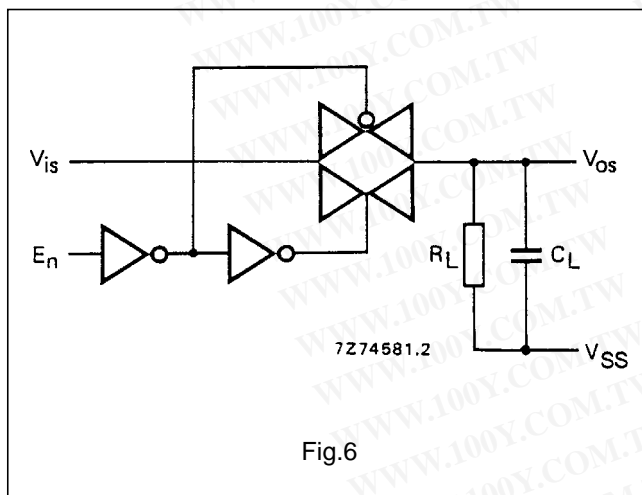
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	V_{DD} V	TYPICAL FORMULA FOR P (μ W)	
Dynamic power dissipation per package (P)	5 10 15	$800 f_i + \sum (f_o C_L) \times V_{DD}^2$ $3\ 500 f_i + \sum (f_o C_L) \times V_{DD}^2$ $10\ 100 f_i + \sum (f_o C_L) \times V_{DD}^2$	where f_i = input freq. (MHz) f_o = output freq. (MHz) C_L = load capacitance (pF) $\sum (f_o C_L)$ = sum of outputs V_{DD} = supply voltage (V)

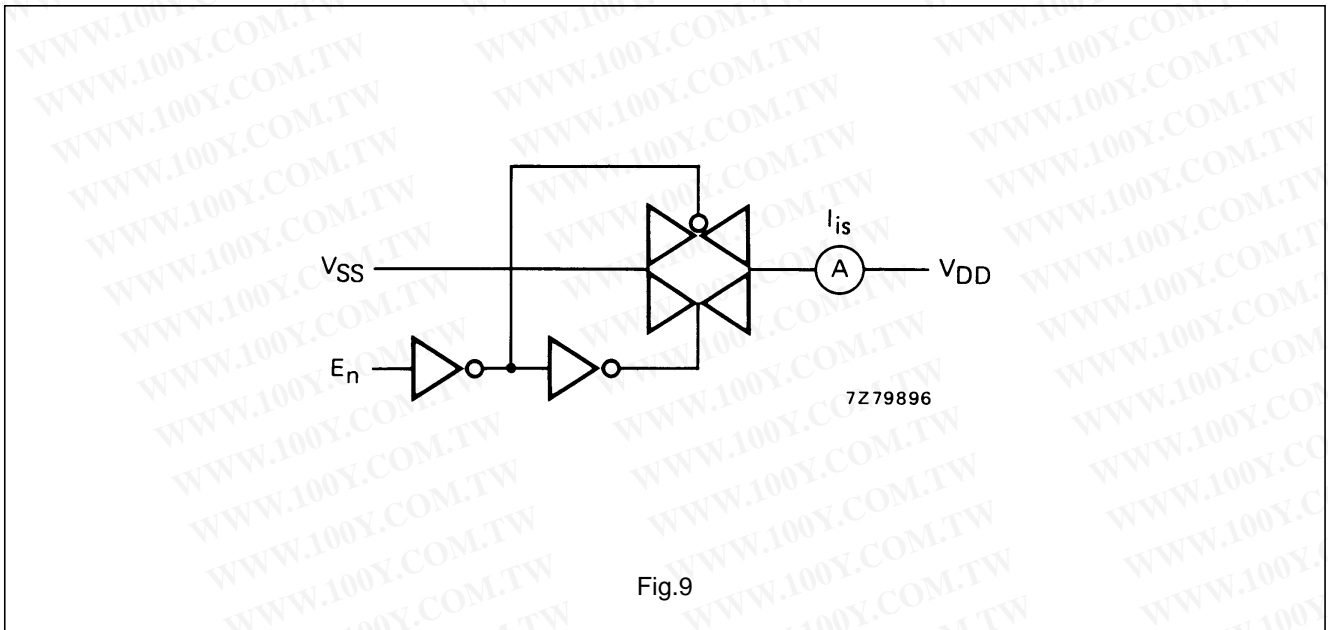
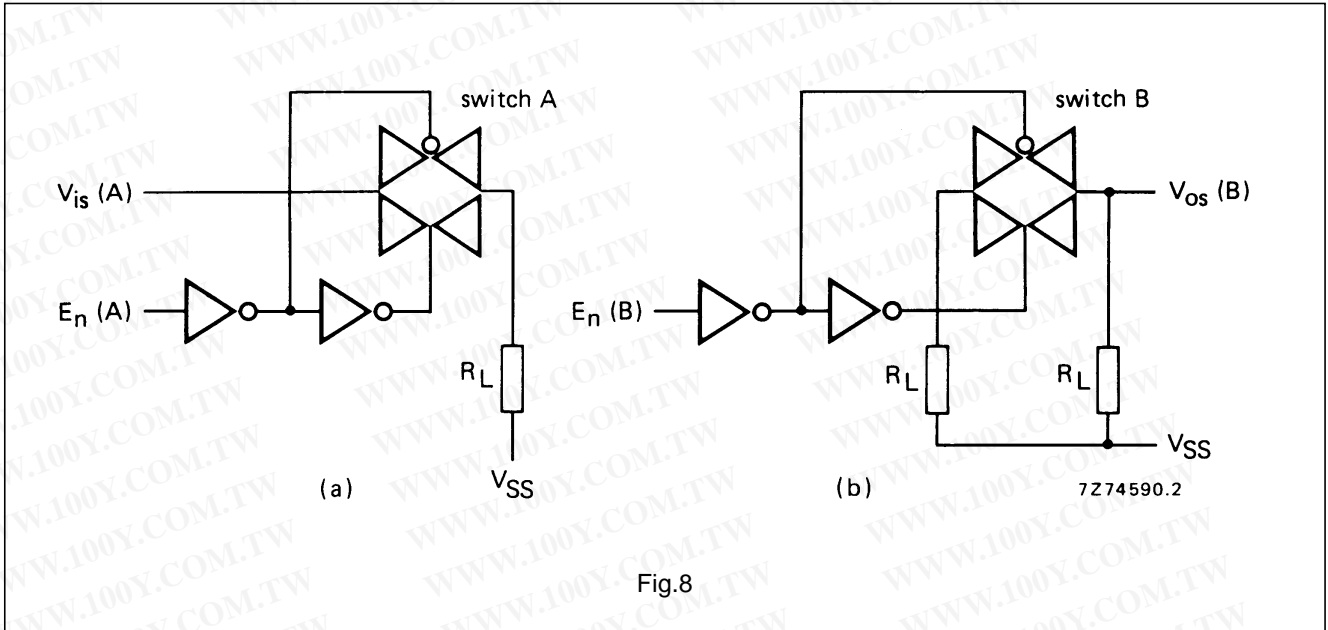
Notes

- V_{is} is the input voltage at a Y or Z terminal, whichever is assigned as input.
- V_{os} is the output voltage at a Y or Z terminal, whichever is assigned as output.
- $R_L = 10\text{ k}\Omega$ to V_{SS} ; $C_L = 50\text{ pF}$ to V_{SS} ; $E_n = V_{DD}$; $V_{is} = V_{DD}$ (square-wave); see Figs 6 and 10.
- $R_L = 10\text{ k}\Omega$; $C_L = 50\text{ pF}$ to V_{SS} ; $E_n = V_{DD}$ (square-wave);
 $V_{is} = V_{DD}$ and R_L to V_{SS} for t_{PHZ} and t_{PZH} ;
 $V_{is} = V_{SS}$ and R_L to V_{DD} for t_{PLZ} and t_{PZL} ; see Figs 6 and 11.
- $R_L = 10\text{ k}\Omega$; $C_L = 15\text{ pF}$; $E_n = V_{DD}$; $V_{is} = \frac{1}{2} V_{DD(p-p)}$ (sine-wave, symmetrical about $\frac{1}{2} V_{DD}$); $f_{is} = 1\text{ kHz}$; see Fig.7.
- $R_L = 1\text{ k}\Omega$; $V_{is} = \frac{1}{2} V_{DD(p-p)}$ (sine-wave, symmetrical about $\frac{1}{2} V_{DD}$);
 $20 \log \frac{V_{os}(B)}{V_{is}(A)} = -50\text{ dB}$; $E_n(A) = V_{SS}$; $E_n(B) = V_{DD}$; see Fig. 8.
- $R_L = 10\text{ k}\Omega$ to V_{SS} ; $C_L = 15\text{ pF}$ to V_{SS} ; $E_n = V_{DD}$ (square-wave); crosstalk is $|V_{os}|$ (peak value); see Fig.6.
- $R_L = 1\text{ k}\Omega$; $C_L = 5\text{ pF}$; $E_n = V_{SS}$; $V_{is} = \frac{1}{2} V_{DD(p-p)}$ (sine-wave, symmetrical about $\frac{1}{2} V_{DD}$);
 $20 \log \frac{V_{os}}{V_{is}} = -50\text{ dB}$; see Fig. 7.
- $R_L = 1\text{ k}\Omega$; $C_L = 5\text{ pF}$; $E_n = V_{DD}$; $V_{is} = \frac{1}{2} V_{DD(p-p)}$ (sine-wave, symmetrical about $\frac{1}{2} V_{DD}$);
 $20 \log \frac{V_{os}}{V_{is}} = -3\text{ dB}$; see Fig. 7.



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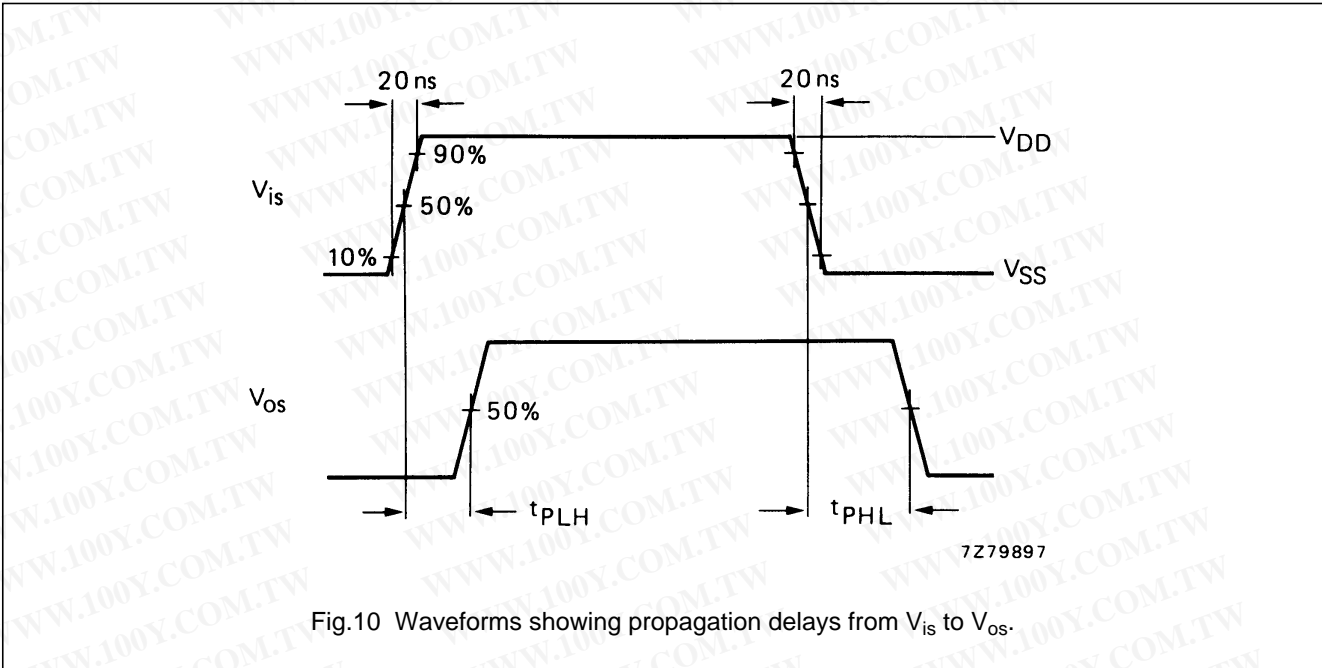
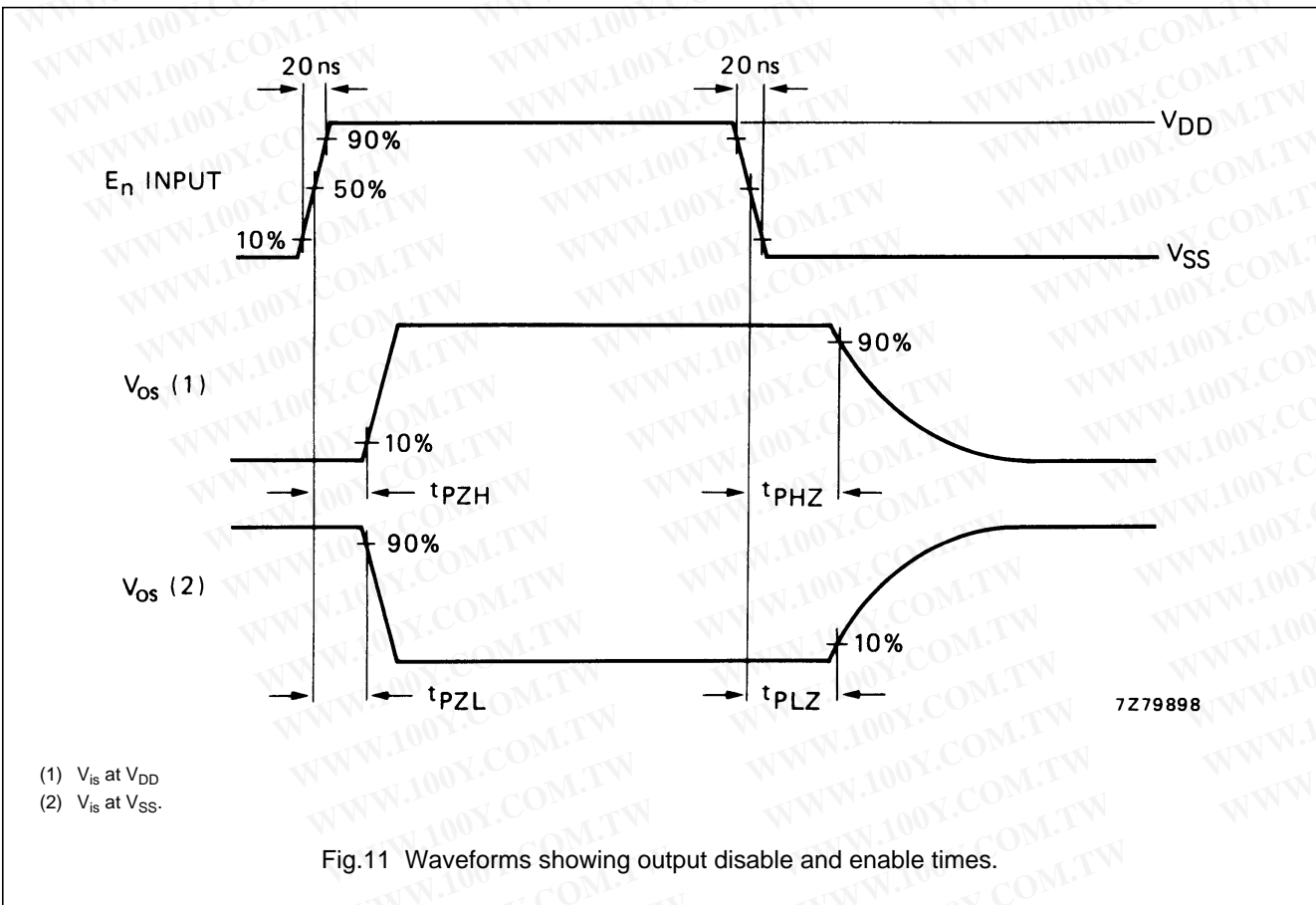


Fig.10 Waveforms showing propagation delays from V_{is} to V_{os} .



- (1) V_{is} at V_{DD}
- (2) V_{is} at V_{SS} .

Fig.11 Waveforms showing output disable and enable times.